



NTZS3151PT1H Information



For Reference Only

Part Number NTZS3151PT1H
Manufacturer ON Semiconductor

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET P-CH 20V 0.86A SOT563

Package SOT-563, SOT-666

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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Certified Quality

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NTZS3151PT1H Specifications

Manufacturer Part Number NTZS3151PT1H Manufacturer ON Semiconductor Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package SOT-563, SOT-666 Series - FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 20V Current - Continuous Drain (Id) @ 25°C 860mA (Ta) Drive Voltage (Max Rds On, Min Rds On) 1.8V, 4.5V Vgs(th) (Max) @ Id 1V @ 250µA Gate Charge (Qg) (Max) @ Vgs 5.6nC @ 4.5V Input Capacitance (Ciss) (Max) @ Vds 458pF @ 16V Vgs (Max) ±8F @ 16V Vgs (Max) 150 mOhm @ 950mA, 4.5V Power Dissipation (Max) 170mW (Ta) Rds On (Max) @ Id, Vgs 150 mOhm @ 950mA, 4.5V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package SOT-563-6 Package / Case SOT-563, SOT-666		
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Package SOT-563, SOT-666 Series - FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 20V Current - Continuous Drain (Id) @ 25°C 860mA (Ta) Drive Voltage (Max Rds On, Min Rds On) 1.8V, 4.5V Vgs(th) (Max) @ Id 1V @ 250μA Gate Charge (Qg) (Max) @ Vgs 5.6nC @ 4.5V Input Capacitance (Ciss) (Max) @ Vds 458pF @ 16V Vgs (Max) ±8V FET Feature - Power Dissipation (Max) 170mW (Ta) Rds On (Max) @ Id, Vgs 150 mOhm @ 950mA, 4.5V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package SOT-563-6 Package / Case SOT-563, SOT-666	Manufacturer	ON Semiconductor
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Series - FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 20V Current - Continuous Drain (Id) @ 25°C 860mA (Ta) Drive Voltage (Max Rds On, Min Rds On) 1.8V, 4.5V Vgs(th) (Max) @ Id 1V @ 250µA Gate Charge (Qg) (Max) @ Vgs 5.6nC @ 4.5V Input Capacitance (Ciss) (Max) @ Vds 458pF @ 16V Vgs (Max) ±8V FET Feature - Power Dissipation (Max) 170mW (Ta) Rds On (Max) @ Id, Vgs 150 mOhm @ 950mA, 4.5V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package SOT-563-6 Package / Case SOT-563, SOT-666		Transistors - FETs, MOSFETs - Single
FET TypeP-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)20VCurrent - Continuous Drain (Id) @ 25°C860mA (Ta)Drive Voltage (Max Rds On, Min Rds On)1.8V, 4.5VVgs(th) (Max) @ Id1V @ 250μAGate Charge (Qg) (Max) @ Vgs5.6nC @ 4.5VInput Capacitance (Ciss) (Max) @ Vds458pF @ 16VVgs (Max)±8VFET Feature-Power Dissipation (Max)170mW (Ta)Rds On (Max) @ Id, Vgs150 mOhm @ 950mA, 4.5VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageSOT-563-6Package / CaseSOT-563, SOT-666	Package	SOT-563, SOT-666
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)20VCurrent - Continuous Drain (Id) @ 25°C860mA (Ta)Drive Voltage (Max Rds On, Min Rds On)1.8V, 4.5VVgs(th) (Max) @ Id1V @ 250μAGate Charge (Qg) (Max) @ Vgs5.6nC @ 4.5VInput Capacitance (Ciss) (Max) @ Vds458pF @ 16VVgs (Max)±8VFET Feature-Power Dissipation (Max)170mW (Ta)Rds On (Max) @ Id, Vgs150 mOhm @ 950mA, 4.5VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageSOT-563-6Package / CaseSOT-563, SOT-666	Series	-
Drain to Source Voltage (Vdss)20VCurrent - Continuous Drain (Id) @ 25°C860mA (Ta)Drive Voltage (Max Rds On, Min Rds On)1.8V, 4.5VVgs(th) (Max) @ Id1V @ 250μAGate Charge (Qg) (Max) @ Vgs5.6nC @ 4.5VInput Capacitance (Ciss) (Max) @ Vds458pF @ 16VVgs (Max)±8VFET Feature-Power Dissipation (Max)170mW (Ta)Rds On (Max) @ Id, Vgs150 mOhm @ 950mA, 4.5VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageSOT-563-6Package / CaseSOT-563, SOT-666	FET Type	P-Channel
Current - Continuous Drain (Id) @ 25°C B60mA (Ta) Drive Voltage (Max Rds On, Min Rds On) 1.8V, 4.5V Vgs(th) (Max) @ Id 1V @ 250µA Gate Charge (Qg) (Max) @ Vgs 5.6nC @ 4.5V Input Capacitance (Ciss) (Max) @ Vds 458pF @ 16V Vgs (Max) #8V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 150 mOhm @ 950mA, 4.5V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case SOT-563, SOT-666	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)1.8V, 4.5VVgs(th) (Max) @ Id1V @ 250μAGate Charge (Qg) (Max) @ Vgs5.6nC @ 4.5VInput Capacitance (Ciss) (Max) @ Vds458pF @ 16VVgs (Max)±8VFET Feature-Power Dissipation (Max)170mW (Ta)Rds On (Max) @ Id, Vgs150 mOhm @ 950mA, 4.5VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageSOT-563-6Package / CaseSOT-563, SOT-666	Drain to Source Voltage (Vdss)	20V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case SOT-563, SOT-666	Current - Continuous Drain (Id) @ 25°C	860mA (Ta)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 458pF @ 16V Vgs (Max) ±8V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 150 mOhm @ 950mA, 4.5V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case SOT-563, SOT-666	Drive Voltage (Max Rds On, Min Rds On)	1.8V, 4.5V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 150 mOhm @ 950mA, 4.5V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case SOT-563, SOT-666	Vgs(th) (Max) @ Id	1V @ 250μA
Vgs (Max)±8VFET Feature-Power Dissipation (Max)170mW (Ta)Rds On (Max) @ Id, Vgs150 mOhm @ 950mA, 4.5VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageSOT-563-6Package / CaseSOT-563, SOT-666	Gate Charge (Qg) (Max) @ Vgs	5.6nC @ 4.5V
FET Feature - Power Dissipation (Max) 170mW (Ta) Rds On (Max) @ Id, Vgs 150 mOhm @ 950mA, 4.5V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package SOT-563-6 Package / Case SOT-563, SOT-666	Input Capacitance (Ciss) (Max) @ Vds	458pF @ 16V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 150 mOhm @ 950mA, 4.5V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package SOT-563-6 Package / Case SOT-563, SOT-666	Vgs (Max)	±8V
Rds On (Max) @ Id, Vgs150 mOhm @ 950mA, 4.5VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageSOT-563-6Package / CaseSOT-563, SOT-666	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package SOT-563-6 Package / Case SOT-563, SOT-666	Power Dissipation (Max)	170mW (Ta)
Mounting Type Surface Mount Supplier Device Package SOT-563-6 Package / Case SOT-563, SOT-666	Rds On (Max) @ Id, Vgs	150 mOhm @ 950mA, 4.5V
Supplier Device Package SOT-563-6 Package / Case SOT-563, SOT-666	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case SOT-563, SOT-666	Mounting Type	Surface Mount
	Supplier Device Package	SOT-563-6
Report errors?	Package / Case	SOT-563, SOT-666
		Report errors?

NTZS3151PT1H Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

NTZS3151PT1H Payment Methods



















NTZS3151PT1H Shipping Methods













If you have any question about NTZS3151PT1H, please do not hesitate to contact us!

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